

MOTT-HUBBARD LOCALIZATION IN A MODEL
OF THE ELECTRONIC SUBSYSTEM
OF DOPED FULLERIDES

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S u m m a r y

A microscopical model of doped fulleride electronic subsystem taking the triple orbital degeneracy of energy states into account is considered within the configurational-operator approach. Using the Green function method, the energy spectrum at the integer band filling $n = 1$ corresponding to AC_{60} compounds is calculated. A possible correlation-driven metal-insulator transition within the model is discussed.